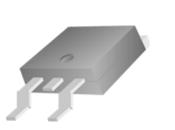
Analog Power AM20N20-125D

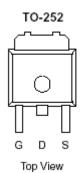
## N-Channel 200-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY				
$V_{DS}(V)$	$r_{DS(on)} m(\Omega)$	$I_{D}(A)$		
200	$260 @ V_{GS} = 10V$	12		
	300 @ V <sub>GS</sub> = 5.5V	11		

- Low r<sub>DS(on)</sub> provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe DPAK saves board space
- Fast switching speed
- High performance trench technology





 $^{\rm o}$ C

-55 to 175

T<sub>J</sub>, T<sub>stg</sub>

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Units
Drain-Source Voltage		$V_{DS}$	200	V
Gate-Source Voltage		$V_{GS}$	±20	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
Continuous Drain Current <sup>a</sup>	$T_C=25^{\circ}C$	$I_D$	15	
Pulsed Drain Current <sup>b</sup>		$I_{DM}$	36	A
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	30	A
Power Dissipation <sup>a</sup>	$T_C=25^{\circ}C$	$P_{D}$	50	W

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient <sup>a</sup>	$R_{ heta JA}$	50	°C/W		
Maximum Junction-to-Case	$R_{ heta JC}$	3.0	°C/W		

## Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Operating Junction and Storage Temperature Range

Analog Power AM20N20-125D

SPECIFICATIONS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)							
Danamatan	C	T4 C 144	Limits			T I 94	
Parameter	Symbol	<b>Test Conditions</b>	Min	Тур	Max	Unit	
Static							
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	1.0			V	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = 20 \text{ V}$			±10	μΑ	
Zero Gate Voltage Drain Current	ī	$V_{DS} = 160 \text{ V}, V_{GS} = 0 \text{ V}$			1	μА	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 160 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25		
On-State Drain Current <sup>A</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	34			A	
David Samuel On Braintan A		$V_{GS} = 10 \text{ V}, I_D = 9.2 \text{ A}$			260	mΩ	
Drain-Source On-Resistance <sup>A</sup>	r <sub>DS(on)</sub>	$V_{GS} = 5.5 \text{ V}, I_D = 6.1 \text{ A}$			300		
Forward Tranconductance <sup>A</sup>	${f g}_{ m fs}$	$V_{DS} = 40 \text{ V}, I_D = 5.5 \text{ A}$		4.4		S	
Diode Forward Voltage	$V_{SD}$	$I_S = 9 \text{ A}, V_{GS} = 0 \text{ V}$		1.1		V	
Dynamic <sup>b</sup>							
Total Gate Charge	$Q_{g}$	V - 25 V V - 10 V		8			
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 25 \text{ V}, V_{GS} = 10 \text{ V},$ $I_{D} = 9 \text{ A}$		2	nC		
Gate-Drain Charge	$Q_{\mathrm{gd}}$	1 <sub>D</sub> = 9 A		2			
Turn-On Delay Time	$t_{d(on)}$			3			
Rise Time	$t_{\mathrm{r}}$	$V_{DD} = 100 \; \text{V},  R_L = 25 \; \Omega \;$ , ID = 9 A,		3		C	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 V$		40		nS	
Fall-Time	$t_{\mathrm{f}}$			21			

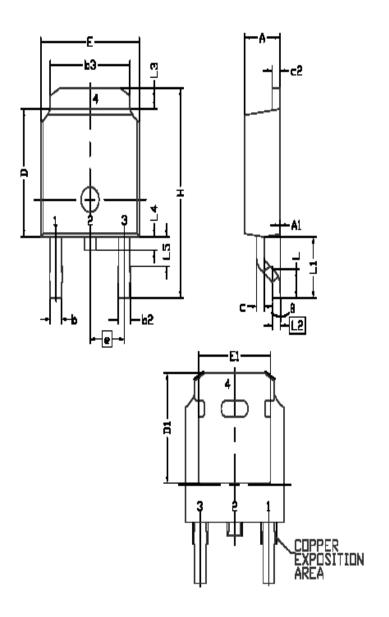
## Notes

- a. Pulse test:  $PW \le 300$ us duty cycle  $\le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

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## Package Information



OMMODI.	DIMENS:	IINAL F	RECINTS
LIDEMY2	MIN	2	MAX
Ε	6.40	6.60	6.731
_	1.40	1.52	1.77
L1			EF.
L2	0,	508 BS	Ç
L3	0.89		1.27
L4	0.64	I	13
L5	1	1	-
D	6.00	6.10	6'553
H	9.40	10,00	10.40
Ь	0.64	0.76	0.88
52	0.77	0.84	1.14
b3	5.21	5.34	5.46
•	2	286 BS	3
Α	2.20	2.30	5'38
A1	0		0.127
С	0.45	<b>5</b> 50	060
c2	0.45	0.50	0.58
Di	5.30		-
EL	4.40	I	I
8	ď	1	10*